

WHAT IS CLAIMED IS:

1. A dual damascene partial gap fill polymer fabrication process, comprising:

providing a substrate having a conductive layer therein;

forming a dielectric layer over the substrate and conductive layer;

5 forming at least one via hole in the dielectric layer, to expose a portion of the conductive layer;

covering the dielectric layer with a gap fill polymer, to fill the via hole;

performing a chemical mechanical polishing step to remove the gap fill polymer layer on the outside of the via hole;

10 performing an etching step to remove a portion of the gap fill polymer layer remaining on the inside of the via hole, forming a partial gap fill polymer;

performing a lithographic process to form a photoresist layer having an opening above the dielectric layer, wherein the trench exposes the via hole and partial gap fill polymer;

15 etching a portion of the dielectric layer exposed in the opening, to form a trench in the dielectric layer;

removing the photoresist layer and partial gap fill polymer, to expose a portion of the conductive layer; and

filling the via hole and the trench with a metal material, to simultaneously form a

20 plug and a conductive line.

2. The method of claim 1, wherein forming at least one via hole includes forming an isolated via hole and a dense via hole.

3. The method of claim 1, wherein the etching step includes anisotropic etching.

4. The method of claim 1, wherein the dielectric layer includes a conductive

line.

5. The method of claim 1, wherein a material of the dielectric layer include silicon oxide.

6. The method of claim 1, wherein the dielectric layer includes an organic
5 material having a low dielectric constant.

7. The method of claim 1, further comprising the following steps:
providing a substrate having a conductive layer therein, and a passivation layer
formed over the conductive layer;

sequentially forming a first dielectric layer, a first etching stop layer and second
dielectric layer over the passivation layer;

sequentially patterning the second dielectric layer, the etching stop layer and the
first dielectric layer to form at least one via hole, which exposes a portion of the
passivation layer;

covering the second dielectric layer with a gap fill polymer layer, to fill the via
hole;

performing a chemical mechanical polishing step to remove gap fill polymer layer
on the outside of the via hole;

performing an etching step to remove a portion of the gap fill polymer layer
remaining in the via hole, in order to form a partial gap fill polymer;

20 performing a lithographic process to form a photoresist having an opening above
the second dielectric layer, wherein the trench exposes the via hole and the partial gap
fill polymer;

etching an exposed the second dielectric layer until the etching stop layer is
reached, to form a trench in the second dielectric layer;

removing the photoresist layer and the partial gap fill polymer;

removing the passivation layer on a bottom of the via hole to expose a portion of the dielectric layer; and

filling the trench with a metal material to simultaneously form a plug and a

5 conductive line.

8. The method of claim 7, wherein forming at least one via hole includes forming an isolated via hole and a dense via hole.

9. The method of claim 7, wherein the etching step includes an anisotropic etching.

10. The method of claim 7, wherein the dielectric layer includes a conductive line.

11. The method of claim 7, wherein a material of the conductive layer includes metal.

12. The method of claim 7, wherein materials of the passivation layer and the etching stop layer are the same.

13. The method of claim 12, wherein the materials of the passivation layer and the etching stop layer include silicon nitride.

14. The method of claim 7, wherein materials of the first and second dielectric layers are the same.

20 15. The method of claim 14, wherein the materials of the first and second dielectric layers include silicon oxide.

16. The method of claim 14, wherein the materials of the first and second dielectric layers include an organic material having a low dielectric constant.